

# Effective mass, holes, energy band diagram

## LECTURE 3

- Material classification
- Effective mass
- Parabolic Band Approximation
- Holes
- Bands in real semiconductors
- Constant-energy surfaces
- Energy band diagram

## Sec. 2.7

## Semiconductor, metal, or insulator?

Our  $N=10$  example is for one-electron primitive cells and gives  $N$  states per BAND.

Allowing for spin there are  $2N$  states per band

Silicon has 2 atoms per primitive cell, with 4 valence electrons in each atom,

i.e., 8 electrons per primitive cell and  $8N$  valence electrons in total.

Therefore, the first 4 bands are completely filled (at 0K).

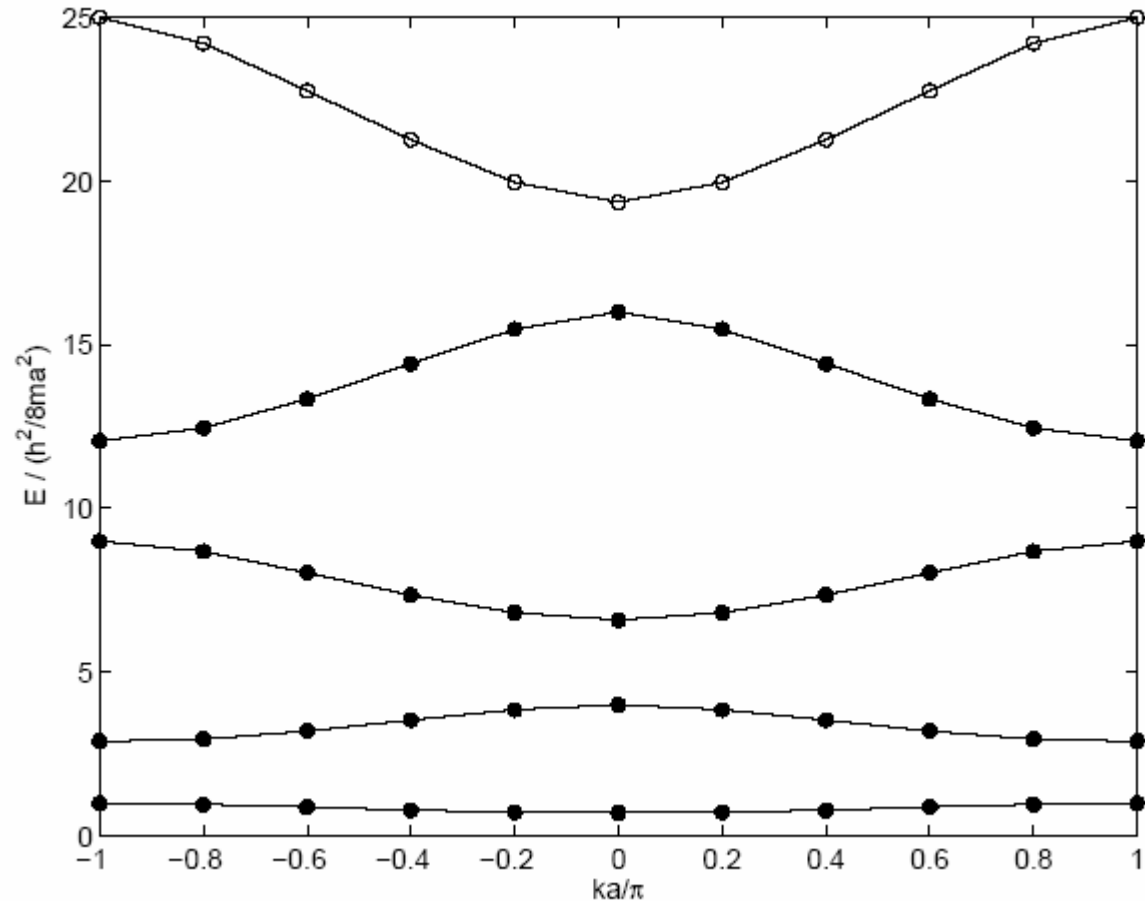
What happens at  $T > 0K$  ?

Where is the BANDGAP?

One possibility for a metal is that the material has  $3N$  valence electrons.

Why does this make a metal?

What makes an insulator?



# Crystal momentum and external force

$$\frac{dE}{dt} = F_{x, \text{ext}} \frac{dx}{dt} = F_{x, \text{ext}} v_x$$

Energy gain from an external force

e.g.,  $F =$

$$v_x = \frac{1}{\hbar} \frac{dE}{dk_x}$$

group velocity  $\equiv$

Implications of using this velocity?

$$\frac{dE}{dt} = \frac{dE}{dk_x} \frac{dk_x}{dt},$$

Chain Rule

$\hbar k$  is the

$$F_{x, \text{ext}} = \frac{d(\hbar k_x)}{dt}.$$

The crystal momentum changes due to

## Sec. 2.9

## Effective mass

$$a_x = \frac{dv_x}{dt} = \frac{1}{\hbar} \frac{d^2 E}{dk_x^2} \frac{dk_x}{dt} = \frac{1}{\hbar^2} \frac{d^2 E}{dk_x^2} \frac{d(\hbar k_x)}{dt}$$

$$a_x = \left[ \frac{1}{\hbar^2} \frac{d^2 E}{dk_x^2} \right] F_{x, \text{ext}} \quad \longrightarrow \quad m_x^*(E) = \left[ \frac{1}{\hbar^2} \frac{d^2 E}{dk_x^2} \right]^{-1}$$

What is the sign of  $m^*$  at the top of the VB?

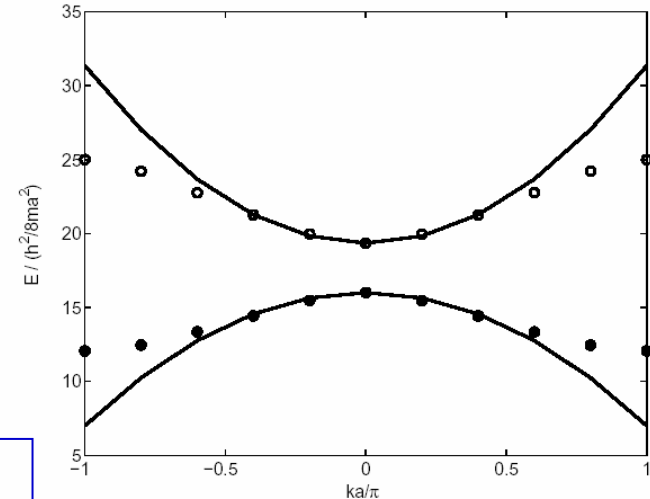
What does this mean?

If  $m^*$  is constant, we have a  band.

Apply such an approximation to our toy bands.

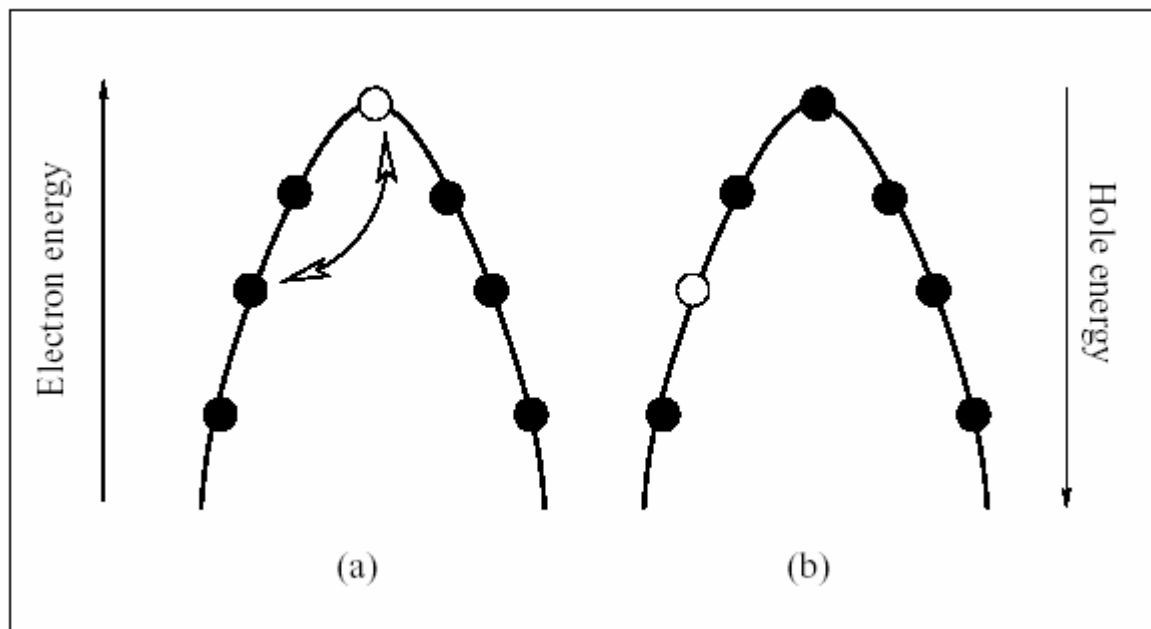
Is it useful to have an approximation that only works near the band extrema?

What is a useful equation for the conduction band?



Sec.  
2.9.1

# Holes



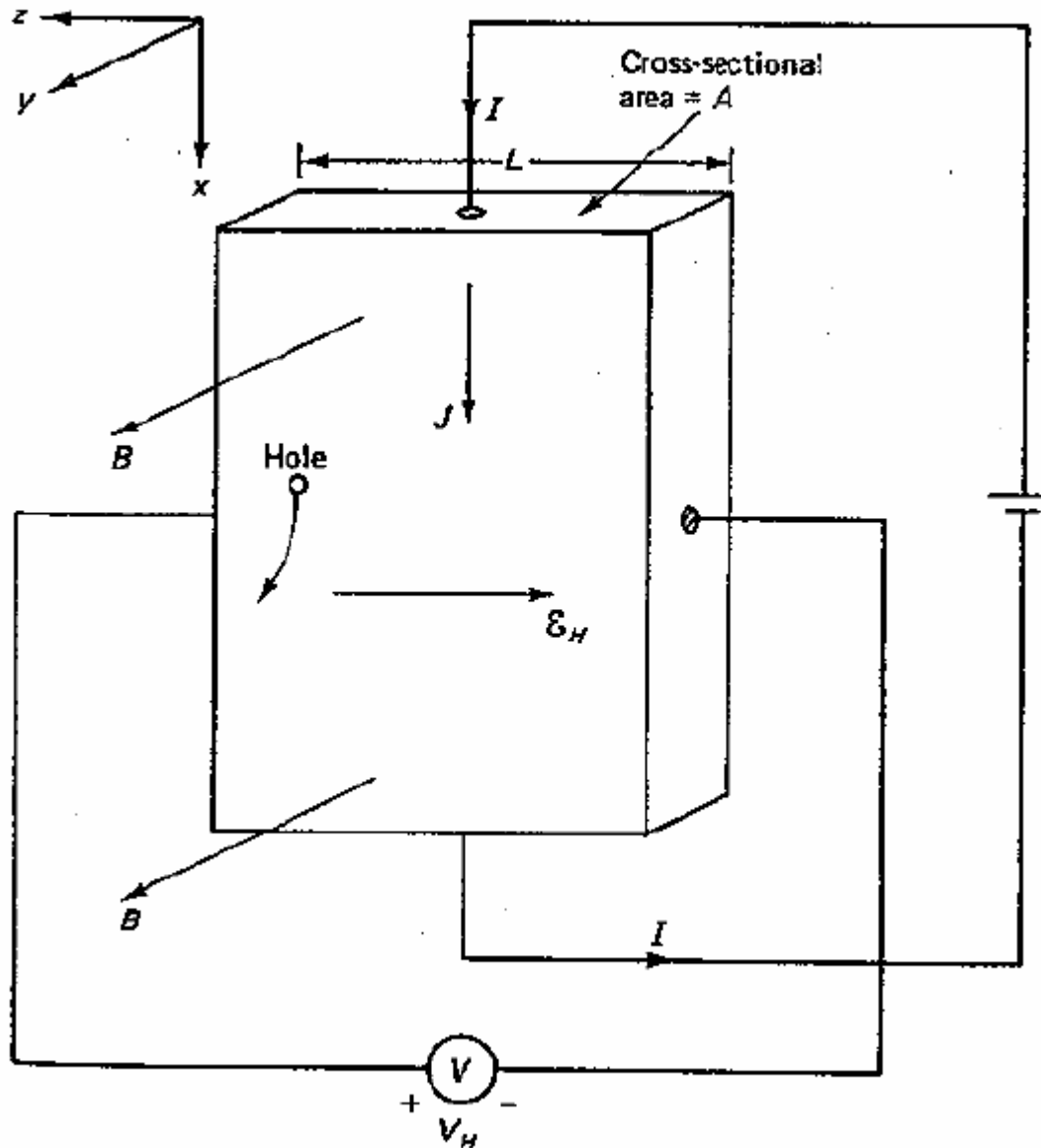
What is the x-axis on this plot?

We can view this excitation event as EITHER a VB electron gaining energy OR as a  gaining energy.

What is the advantage of choosing the latter viewpoint?

What is the charge on a hole?

# The Hall Effect



$$F = \square$$

What is the Hall-Effect voltage when:

1.  $n=p$
2.  $n>p$
3.  $n<p$  ?

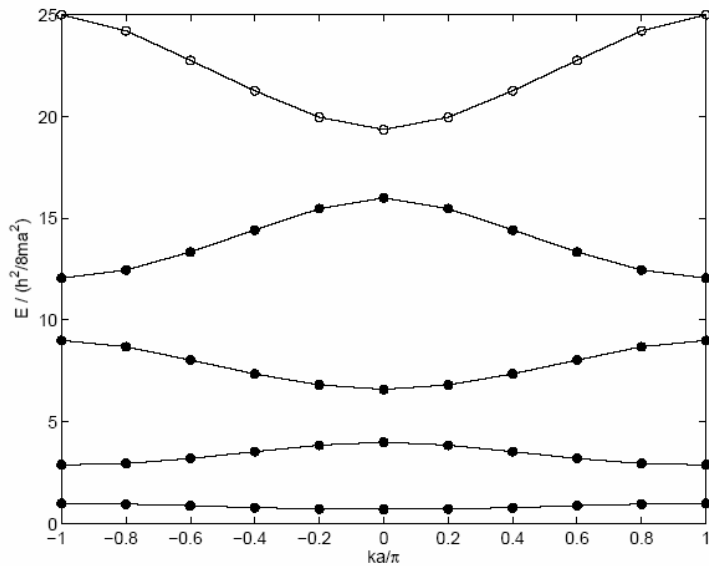
$n$  and  $p$  are, respectively, the concentrations of



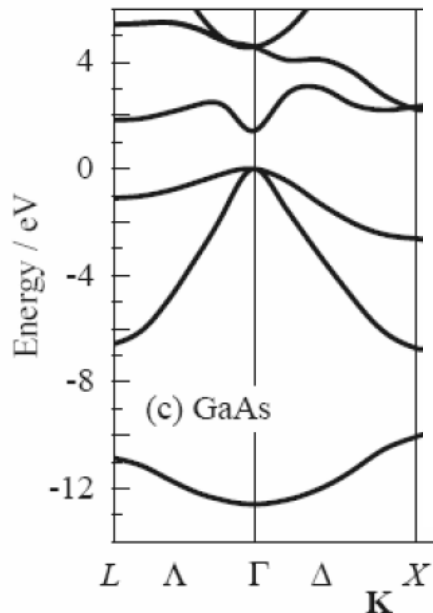
What are their units in 3-D?

## Sec. 2.8

## Energy bands in real materials



This is what we have from our toy model.



This is what you get for real gallium arsenide.

Note:

- 4 (FOUR) bands for valence electrons
- Strange notation for Bloch wavevector

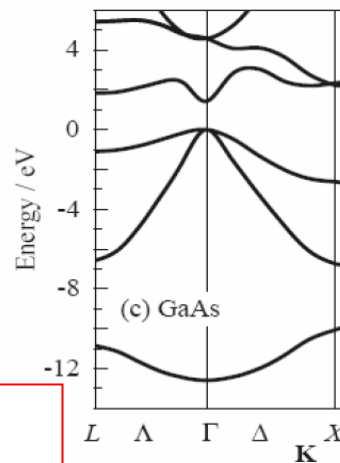
Identify the valence bands.

Why are the curves asymmetrical about the  $\Gamma$  point?

## Sec. 2.8

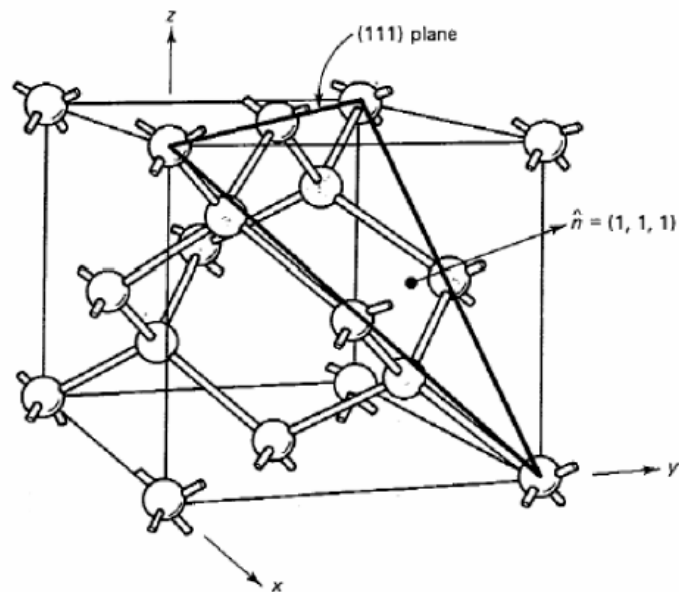
## Labeling directions and planes

Label directions using  
Miller indices.



The directions in k-space (reciprocal space) are perpendicular to the corresponding planes in real space.

What is the label for the front face?





Sec.  
2.10

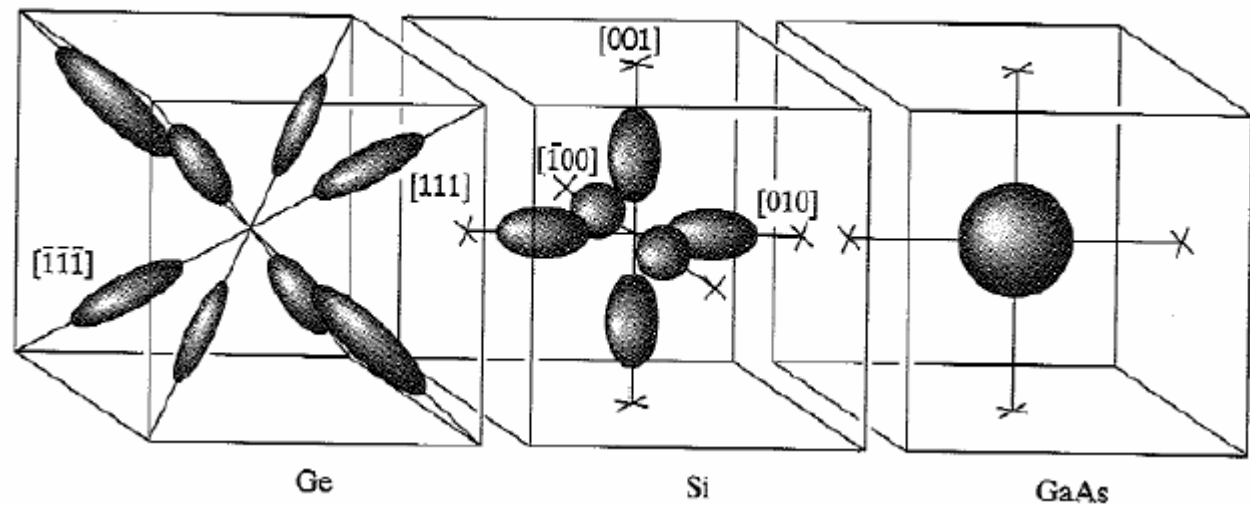
## Constant-energy surfaces

In 3-D structures, the parabolic-effective-mass concept leads naturally to

$$E - E_{C0} = \frac{\hbar^2}{2} \quad \square \quad ,$$

Can you see how degeneracies can occur?

Constant-energy surfaces for electrons in the CB



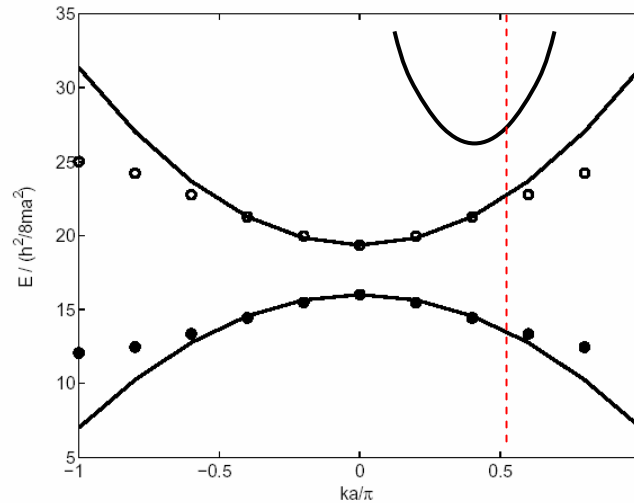
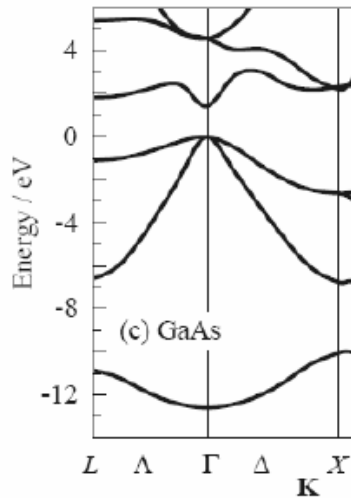
Which axis corresponds to  $k_x$ ?

How many values of  $m_e^*$  for (a) Si, (b) GaAs ?

## Sec. 2.12

## Potential energy

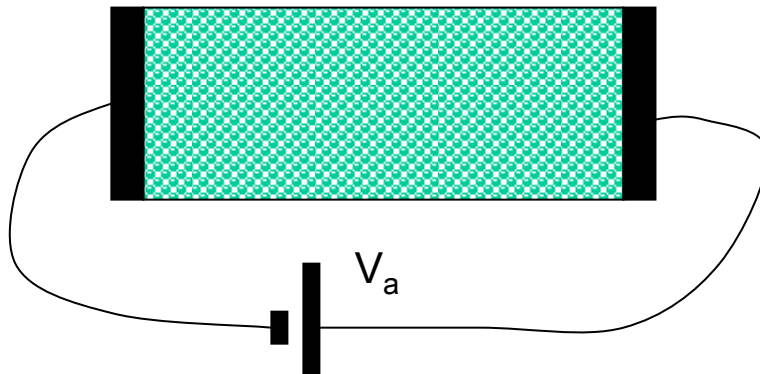
Microscopically:



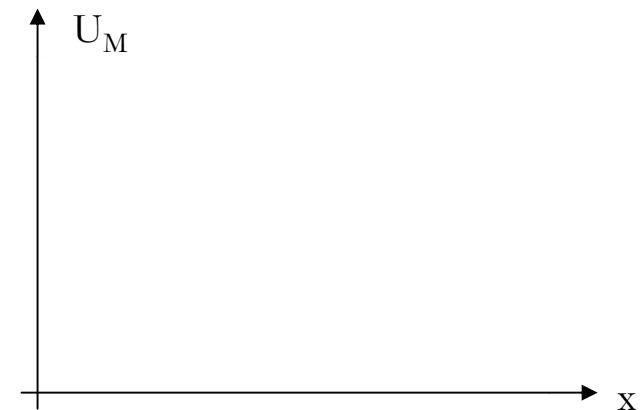
$$E_\nu(k) = E_{C0} + \frac{\hbar^2 k^2}{2m^*}$$

- What is  $\nu$  ?
- Where is  $E_{C0}$  for  $\nu = 1$  ?
- Physically, what is  $E_{C0}$  ?

Macroscopically:



What is  $U_M(x)$ ?  
Sketch it for  
this case.



## Sec. 2.12

## Energy band diagram

Add in the  
macroscopic  
potential energy

$$E = U_M(x) + E_{C0} + \frac{\hbar^2 k^2}{2m^*}$$

$$\equiv E_C(x) + \frac{\hbar^2 k^2}{2m^*},$$

